# MBRS1100T3G, SBRS81100T3G, MBRS190T3G, SBRS8190T3G

# **Schottky Power Rectifier**

## **Surface Mount Power Package**

Schottky Power Rectifiers employ the use of the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes, in surface mount applications where compact size and weight are critical to the system. These state-of-the-art devices have the following features:

#### Features

- Small Compact Surface Mountable Package with J-Bend Leads
- Rectangular Package for Automated Handling
- Highly Stable Oxide Passivated Junction
- High Blocking Voltage 100 Volts
- 175°C Operating Junction Temperature
- Guardring for Stress Protection
- AEC-Q101 Qualified and PPAP Capable
- SBRS8 Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- All Packages are Pb-Free

#### **Mechanical Characteristics**

- Case: Epoxy, Molded
- Weight: 95 mg (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped in 12 mm Tape and Reel, 2,500 units per reel
- Cathode Polarity Band



## **ON Semiconductor®**

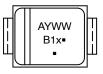
www.onsemi.com

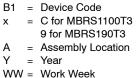
### SCHOTTKY BARRIER RECTIFIER 1.0 AMPERE 90, 100 VOLTS



SMB CASE 403A

#### MARKING DIAGRAM





= Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

## MBRS1100T3G, SBRS81100T3G, MBRS190T3G, SBRS8190T3G

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage MBRS190T3 MBRS1100T3	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	90 100	V
Average Rectified Forward Current $T_L = 163^{\circ}C$ $T_L = 148^{\circ}C$	I <sub>F(AV)</sub>	1.0 2.0	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I <sub>FSM</sub>	50	A
Operating Junction Temperature (Note 1)	TJ	-65 to +175	°C
Voltage Rate of Change	dv/dt	10	V/ns

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance – Junction-to-Lead (T <sub>L</sub> = 25°C)	$R_{\theta JL}$	22	°C/W

#### **ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ( $i_F$ = 1.0 A, $T_J$ = 25°C)	V <sub>F</sub>	0.75	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, TJ = $25^{\circ}$ C) (Rated dc Voltage, T <sub>J</sub> = $100^{\circ}$ C)	I <sub>R</sub>	0.5 5.0	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

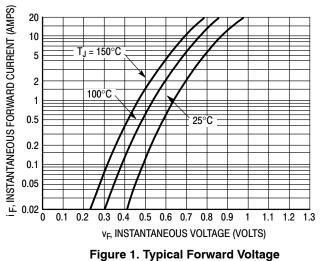
#### **ORDERING INFORMATION**

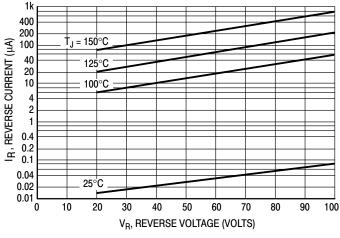
Device Marking		Package	Shipping <sup>†</sup>	
MBRS1100T3G	B1C	SMB (Pb–Free)	2500 / Tape & Reel	
SBRS81100T3G	B1C	SMB (Pb–Free)	2500 / Tape & Reel	
MBRS190T3G	B19	SMB (Pb-Free)	2500 / Tape & Reel	
SBRS8190T3G	B19	SMB (Pb–Free)	2500 / Tape & Reel	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## MBRS1100T3G, SBRS81100T3G, MBRS190T3G, SBRS8190T3G

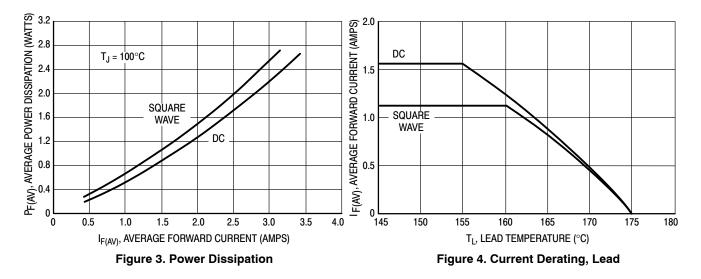






#### Figure 2. Typical Reverse Current\*

\*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these curves if V<sub>R</sub> is sufficient below rated V<sub>R</sub>.



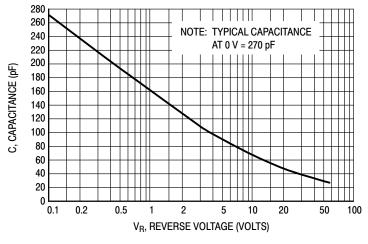
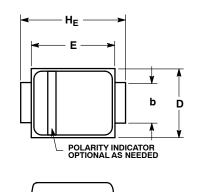


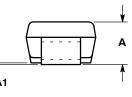
Figure 5. Typical Capacitance

### MBRS1100T3G, SBRS81100T3G, MBRS190T3G, SBRS8190T3G

#### PACKAGE DIMENSIONS

SMB CASE 403A-03 ISSUE J

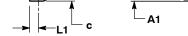




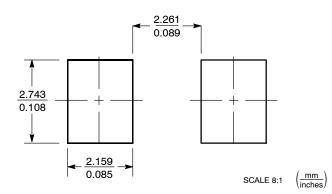
NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH. 3. DIMENSION b SHALL BE MEASURED WITHIN DIMENSION L1.

	MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.95	2.30	2.47	0.077	0.091	0.097
A1	0.05	0.10	0.20	0.002	0.004	0.008
b	1.96	2.03	2.20	0.077	0.080	0.087
С	0.15	0.23	0.31	0.006	0.009	0.012
D	3.30	3.56	3.95	0.130	0.140	0.156
E	4.06	4.32	4.60	0.160	0.170	0.181
HE	5.21	5.44	5.60	0.205	0.214	0.220
L	0.76	1.02	1.60	0.030	0.040	0.063
L1		0.51 REF	0.020 REF			



**SOLDERING FOOTPRINT\*** 



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and the intervent and the intervent of the patient the patient patient of the patient patient of the patient

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative